Unit in mm

TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

155361

ULTRA HIGH SPEED SWITCHING APPLICATION.

Small Package

 $V_{\rm F} = 0.9 V \, ({\rm Typ.})$ Low Forward Voltage

Fast Reverse Recovery Time : $t_{rr} = 1.6ns$ (Typ.)

Small Total Capacitance $: C_T = 0.9 pF (Typ.)$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Maximum (Peak) Reverse Voltage	$v_{ m RM}$	85	V	
Reverse Voltage	$V_{\mathbf{R}}$	80	V	
Maximum (Peak) Forward Current	I_{FM}	300*	mA	
Average Forward Current	IO	100*	mA	
Surge Current (10ms)	$I_{ ext{FSM}}$	2*	A	
Power Dissipation	P	100	mW	
Junction Temperature	T_{j}	125	°C	
Storage Temperature	$T_{ m stg}$	-55~125	°C	

 1.6 ± 0.2 0.8 ± 0.1 0.5 1.0 ± 0.1 ANODE ANODE 2. CATHODE **JEDEC EIAJ** TOSHIBA 1-2S1B

Weight: 2.4mg

* Unit Rating. Total Rating=Unit Rating×1.5

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

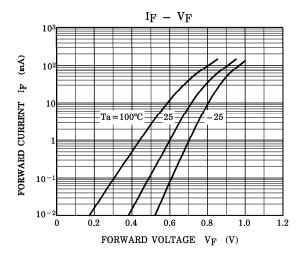
ELECTRICAL CITATOR (TO - 25 C)							
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Forward Voltage	$V_{F(1)}$	$I_{\mathbf{F}} = 1 \text{mA}$	_	0.60		V	
	$V_{F(2)}$	$I_{ extbf{F}} = 10 ext{mA}$		0.72			
	$V_{F(3)}$	$I_{\mathbf{F}} = 100 \text{mA}$	_	0.90	1.20		
Reverse Currunt $ \frac{I_{R(1)}}{I_{R(2)}} $	I _{R (1)}	$V_{ m R}$ = 30 V		_	0.1	μ A	
	I _{R (2)}	$V_R = 80V$	_	_	0.5		
Total Capacitance	$\mathrm{C}_{\mathbf{T}}$	$V_{ m R}$ =0, f=1MHz		0.9	3.0	рF	
Reverse Recovery Time	t _{rr}	I _F =10mA, Fig.1	_	1.6	4.0	ns	

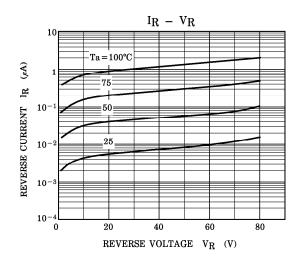
Marking

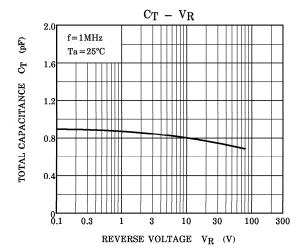


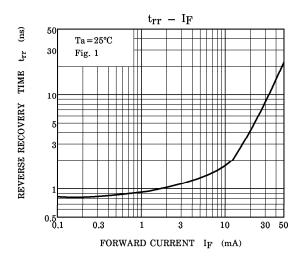
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